



LIST OF REFERENCES CITED BY APPLICANT
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ATTY. DOCKET NO.:

4717-12500

APPLICATION NO.:

10/716,901

APPLICANT:

Bruce FAURE

FILING DATE:

November 18, 2003

GROUP:

2812

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[Handwritten mark]</i>	AA	5,374,564	12/1994	Bruel	437	24	
	AB	6,051,849	4/2000	Davis et al.	257	103	
	AC	6,086,673	7/2000	Molnarq	117	102	
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<i>[Handwritten mark]</i>	AK	EP 1 361 298 A1	11/2003	Europe			X	
	AL	EP 1 298 234 A2	4/2002	Europe			X	
	AM	FR 2 810 159 A1	12/2001	France			X	
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	AP	JP 2002343718 with English Abstract	11/2002	Japan			X	
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EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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	AG							
EXAMINER 				DATE CONSIDERED 12/4/05				
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